



RIBER

Annual Results Presentation 2025

April 8, 2026

RIBER



The Reference Equipment
Manufacturer for Compound
Semiconductors

World Leader in MBE

OUR RESOURCES

Fully mastered industrial know-how

- 100% in-house: design, manufacturing, support
- 120 employees, including 40% managers
- 2 subsidiaries: US and China
- 12% of revenue invested in R&D



OUR CONTRIBUTIONS

A key player in the European value chain

- 70% of suppliers based in France
- A strategic position within the compound semiconductor ecosystem
- Active commitment to environmental and social responsibility

OUR STRENGTHS

A differentiating MBE technology

- More than 800 machines installed worldwide
- The widest range of solutions covering research and production
- €41M in revenues, of which over 90% is international

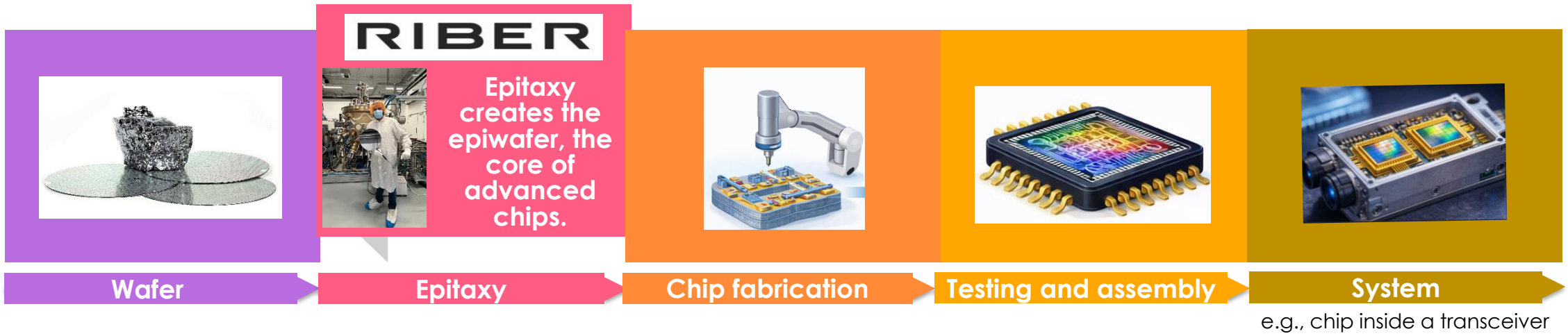
OUR AMBITION

At the heart of strategic technological challenges

- Meeting the needs of advanced semiconductors
- Integrating into silicon photonics
- Contributing to technological sovereignty
- Developing strategic collaborations: joint labs, pilot lines, European projects



Our positioning within our ecosystem



RIBER

Epitaxy creates the epiwafer, the core of advanced chips.

Freiberger
Compound Materials

axt

InPACT

UMS

and more...

IntelliEPI IQE

est
新晨半导体科技(苏州)有限公司
Epi Solution Technology Co., Ltd

and more...

LUMENTUM

Infinera

and more...

III-V lab

innolume

II-VI LASER ENTERPRISE

Almae Technologies

Accelink

TRUMPF

MITSUBISHI ELECTRIC

LASERTEL
a LEONARDO company

and more...

Apple

Facebook

HUAWEI

Google Cloud

and more...

aselsan

NORTHROP GRUMMAN

Raytheon

intel

HISILICON

BAE SYSTEMS

viqo SYSTEM S.A.

NOKIA

and more...



From research to industry: MBE driving innovation

Each generation of RIBER machines has increased productivity, material compatibility, and industrial integration.



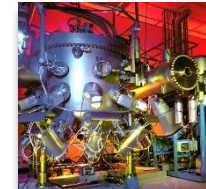
1978

First industrial MBE system



1992

MBE 49
First multi-wafer system for production



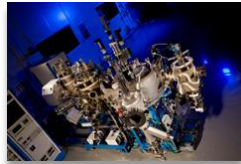
1997

MBE 6000
Transition to mass production



1997

Compact 21
Advanced design for academic systems



2011

Cluster architecture to increase flexibility for academic platforms



2024

MBE 8000
Most productive machine



2025

ROSIE 1
Launch of a system compatible with silicon fabs



2021

SUPRA
First machine dedicated to superconducting materials

2026

ROSIE 2
Production fab Si 300 mm (cluster)

More than 800 systems in operation worldwide



Our markets increasingly oriented toward photonics

DATAKOM / TÉLÉCOM



DEFENSE & SPACE



MEDICAL IMAGING



AUTOMOTIVE



DISPLAYS



UV LEDS



PHOTONICS

- ☐ **Sensors** Ultra-high-sensitivity
- ☐ **Lasers** with high thermal stability / low power consumption / long lifetime

☐ **μLED** with pixel stability

☐ **LED** with the ability to destroy DNA

MICRO-ELECTRONICS

- ☐ **Transistors** with very high-frequency / low-noise / high-speed

Demand is booming in advanced photonics and micro-electronics, driven by AI, datacenters, defense, and quantum technologies.



A complete and integrated offering dedicated to performance and productivity

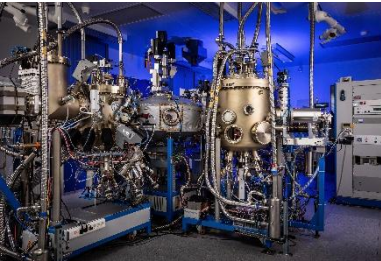
Production machines

MBE 49, MBE 6000
High-productivity platforms for industrial environments



Research machines

Compact 21, MBE 412,
+ SUPRA (exclusive new model)
Flexibility, modularity, and precision for advanced laboratories



Machine for Fab Semi

ROSIE
300 mm; Silicon-compatible
A new strategic market

Services

Process and technical support



Embedded instrumentation

EZ instruments
Proprietary in-situ measurement tools for real-time process control



Components

15 product lines optimized for stability, performance, and flux purity



Software Crystal XE

Advanced control, automation, integrated analytics

RIBER



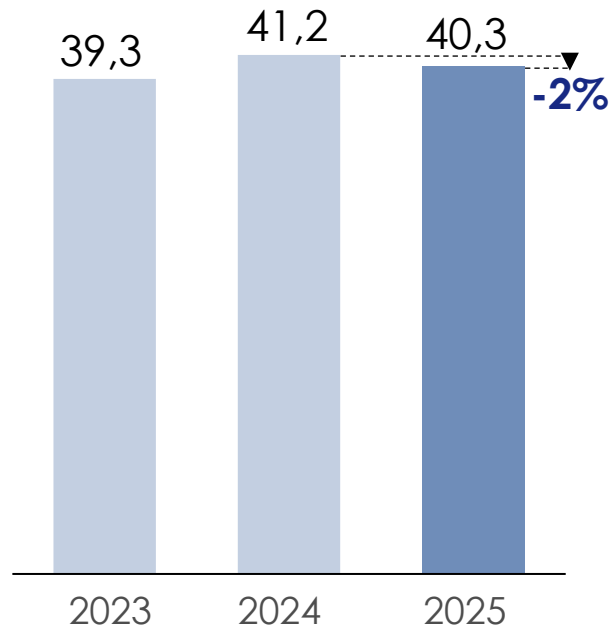
2025 Annual Results

Strengthened financial fundamentals

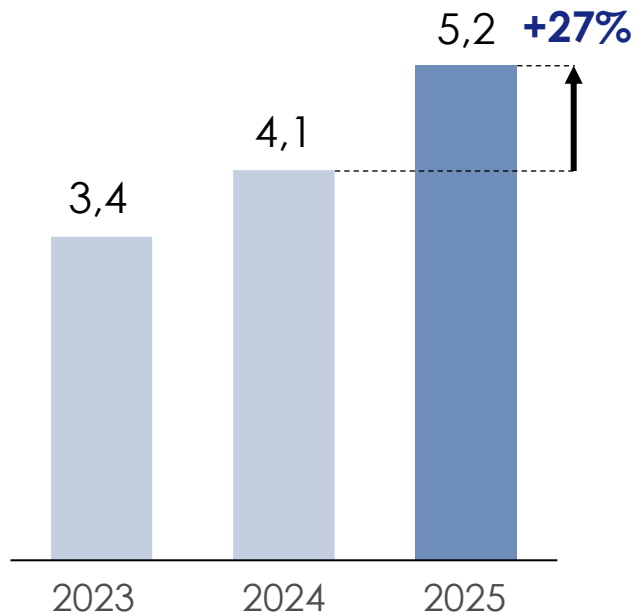


2025: growth in line with the target, improved margins and a solid balance sheet

Revenues (in €m)



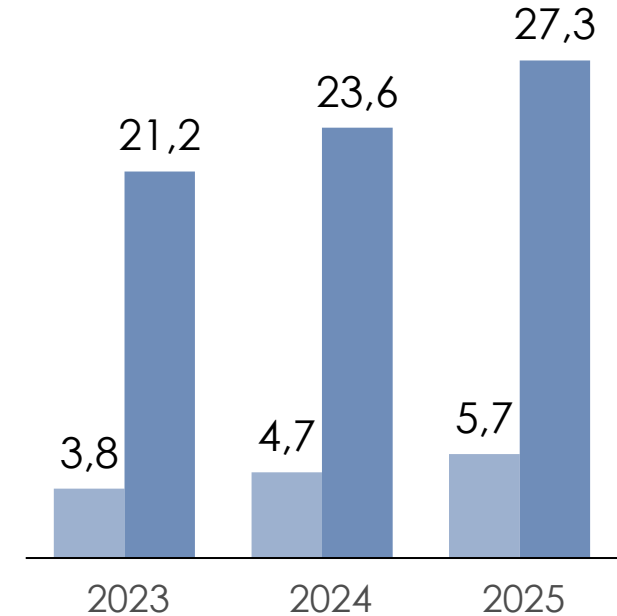
Net income (in €m)



8.7% 10.0% 13.0%

(% of revenues)

Financial structure (in €m)

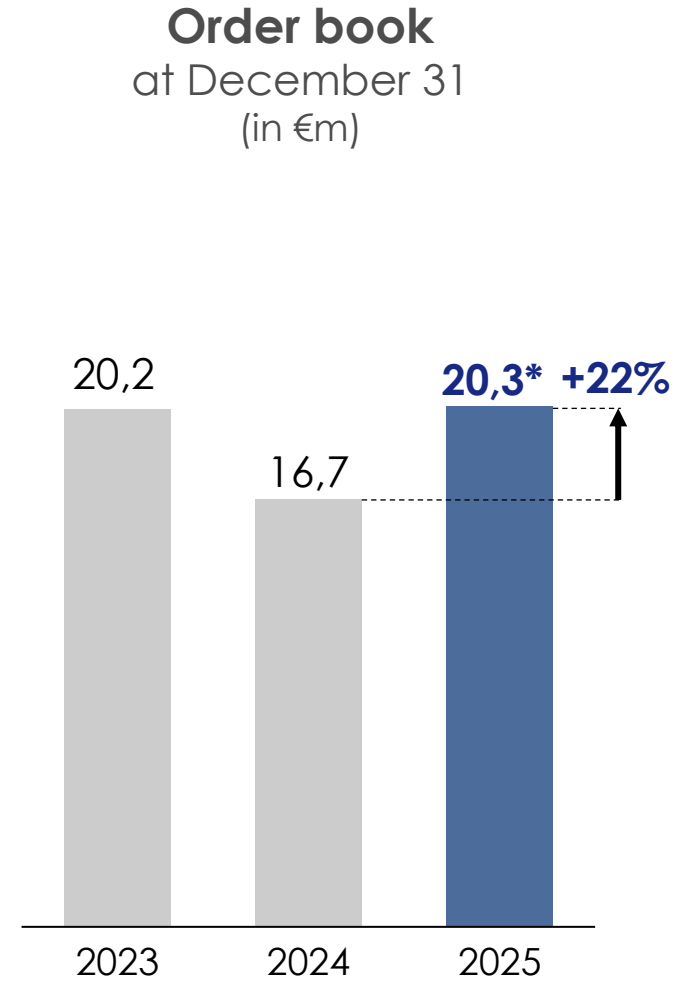
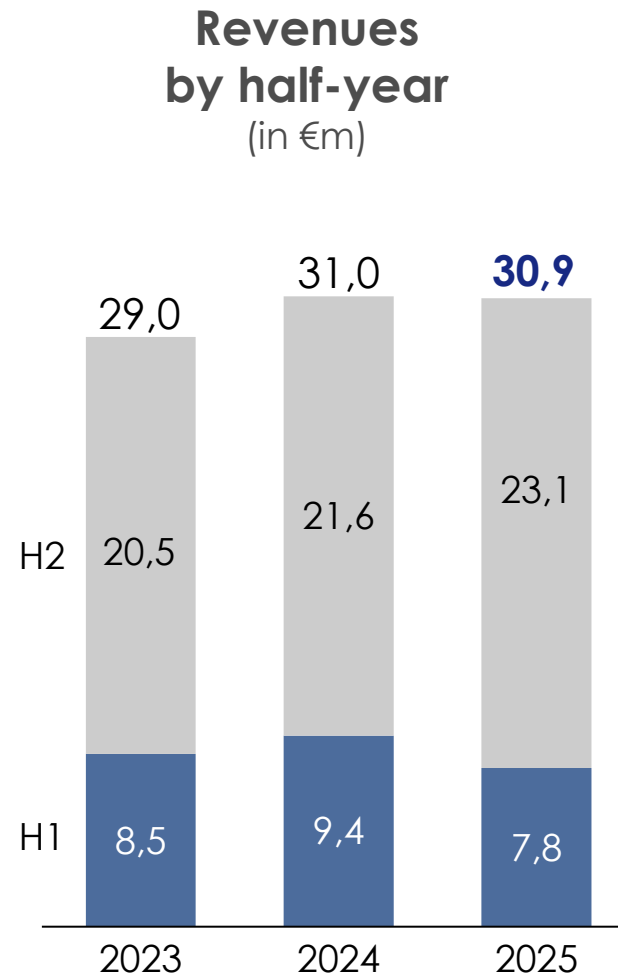


Net cash
Shareholders' equity



Systems Business: Sales momentum and ramp-up of ROSIE

- 12 systems delivered in 2025, including 9 production machines
- First ROSIE unit delivered in H2 2025
- Order backlog at end-2025 up +22%: 6 systems, including 1 ROSIE
- One additional order in Japan in January 2026
- Enhanced visibility thanks to ROSIE and strong commercial momentum

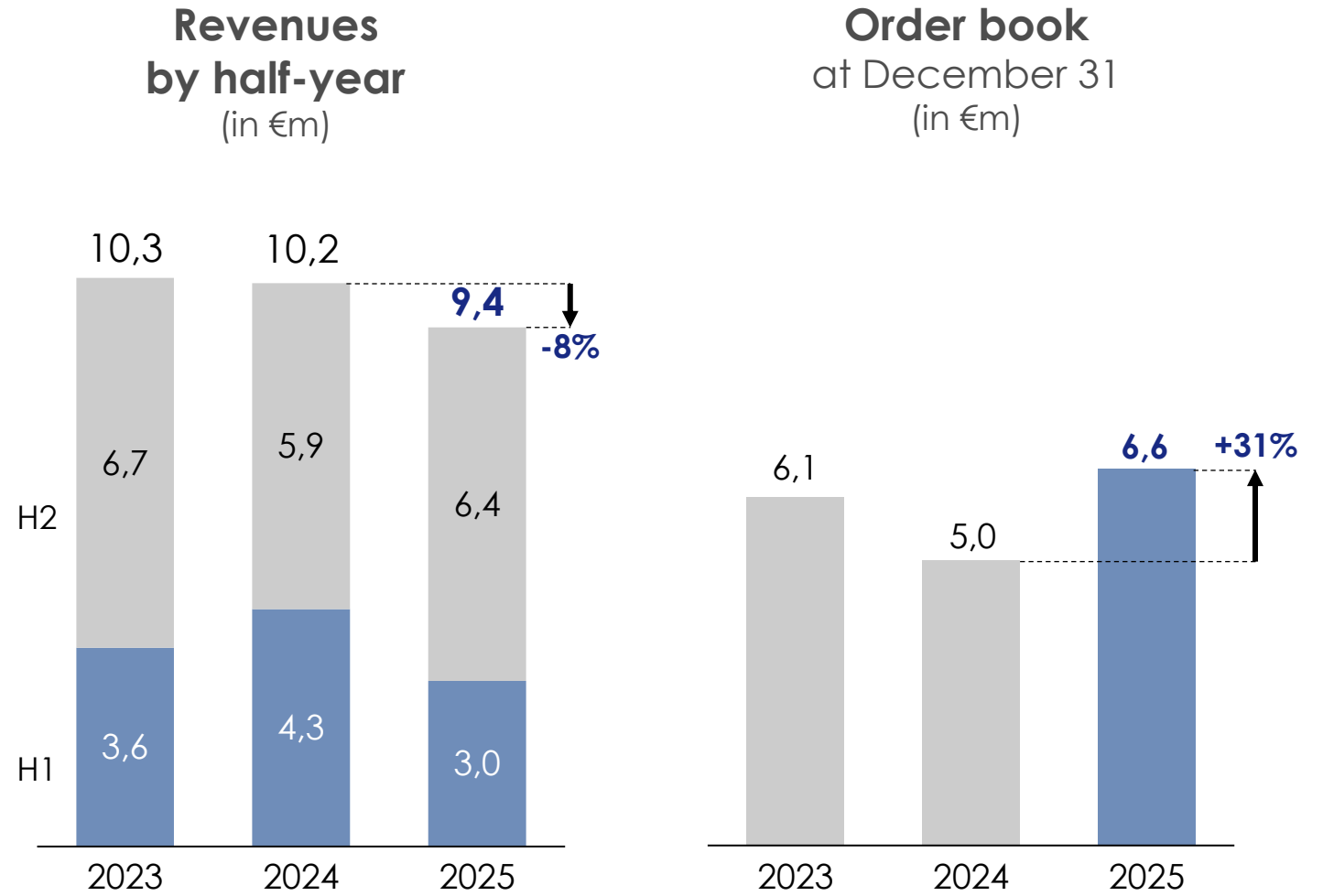


* Excluding the production system order announced in January 2026

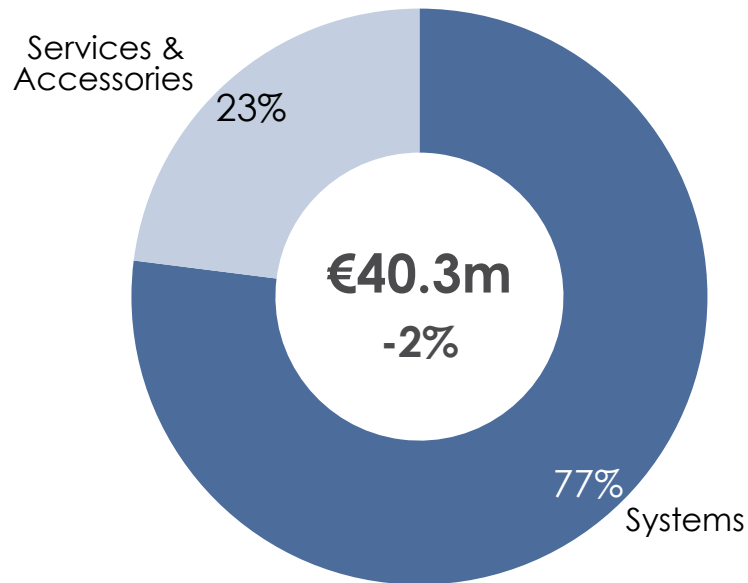


Services and Accessories Business: rebound in H2 and growing order book

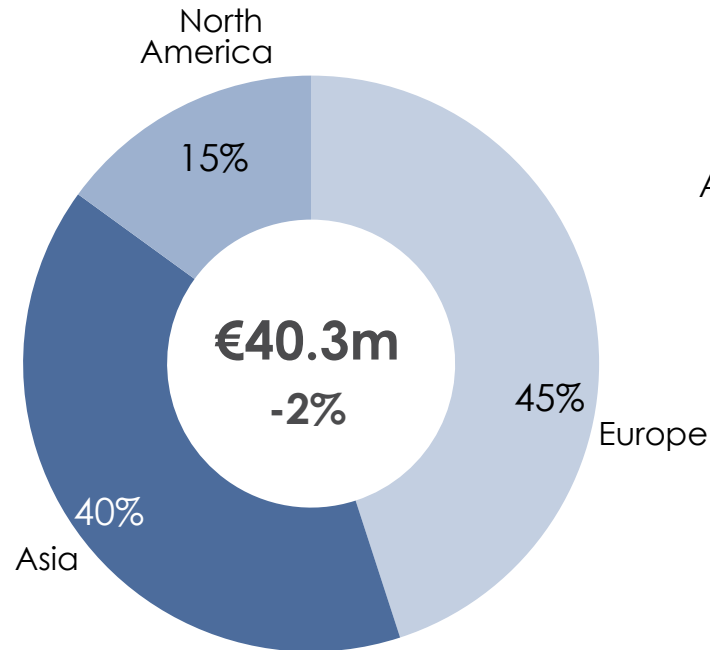
- 2025 revenue impacted by budget restrictions in the United States
- Recovery in H2: +8.5%
- Order book up: €6.6m
- Product plan launched to support the return to growth



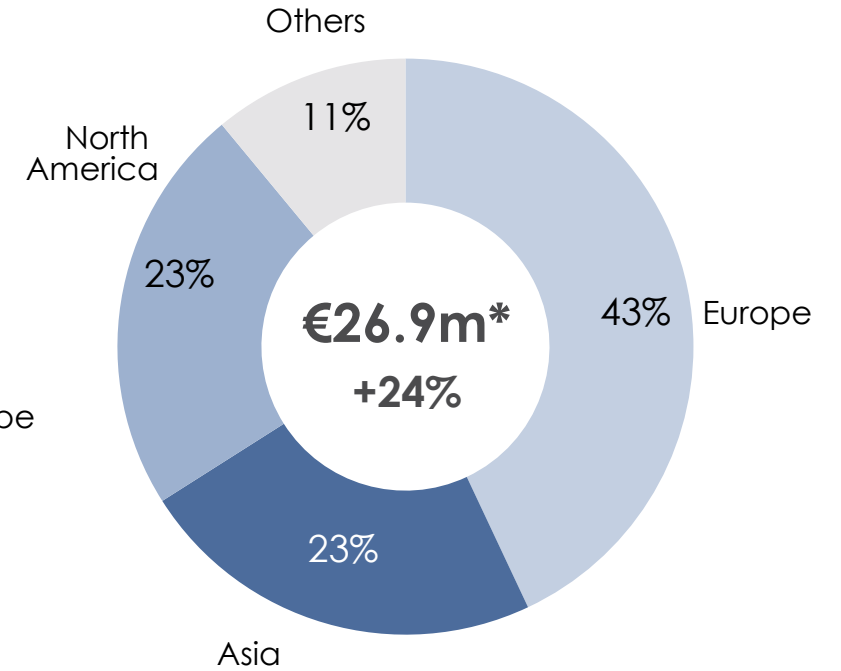
Revenues by activity
as of December 31, 2025



Revenues by geographic area
as of December 31, 2025



Order book by geographic area
as of December 31, 2025



* Excluding the production system order announced in January 2026



2025 Income Statement: Improved margins and strong increase in net income

€40.3m

Revenues
(-2%)

38.6%

Gross margin
(+2,5pts)

€5.1m

Operating income
(+17%)

€5.2m

Net income
(+27%)

13%

Net margin
(+3pts)

(en M€ - normes IFRS)	2025	2024	Δ*
Revenues	40.3	41.2	-2.1%
Systems revenues	30.9	31.0	-0.3%
Services & accessories revenues	9.4	10.2	-7.8%
Gross margin	15.6	14.8	+4.7%
% of revenues	38.6%	36.1%	
Commercial	-3.4	-4.2	
Research and development	-3.2	-2.6	
<i>of which gross R&D expenses</i>	-3.3	-3.9	
<i>of which other items (research tax credit, activation IFRS...)</i>	0.1	1.3	
Administration	-3.9	-3.6	
Income from ordinary operations	5.1	4.5	+13.5%
% of revenues	12.7%	10.9%	
Operating income	5.1	4.4	+16.6%
% of revenues	12.7%	10.6%	
Net income	5.2	4.1	+27.1%
% of revenues	13.0%	10.0%	

Slightly lower revenue. The **gross margin** increased with the product-price-mix evolution.

Maintaining a strong R&D effort (ROSIE, LAAS, CRHEA...) and limited IFRS capitalization of certain eligible expenses.

Significant improvement in **operating margin** driven by controlled operating expenses (+€0.8m).

Net income includes a financial expense of -€0.3m linked to USD exchange-rate effects and a tax income of +€0.4m from the activation of tax loss carryforwards

* change calculated on a k€ basis



Consolidated Balance Sheet: Strengthening of equity and reduction of debt

€27.3m

shareholders' equity
(+€3.7m)

€1.7m

financial debt
(-€2.2m)

€7.5m

cash

€13.4m

Customer advances
(+€1,8m)

€55.4m

Total balance sheet
(+€5.5m)

At December 31 - in €m		2025	2024	Δ
Fixed assets		7.2	7.9	-0.8
Deferred tax assets		2.4	1.4	+0.9
Financial and non-current assets		2.2	2.5	-0.2
Raw material inventories		8.0	8.2	-0.2
Work-in-progress		8.9	9.7	-0.8
Trade receivables		17.9	9.5	+8.4
Other current assets		1.4	2.0	-0.7
Cash		7.5	8.6	-1.1
ASSETS		55.4	49.9	+5.5
Shareholders' equity		27.3	23.6	+3.7
Provisions		2.9	2.1	+0.8
Trade payables		5.3	4.3	+1.1
Customer advances		13.4	11.6	+1.8
Other operating liabilities		4.8	4.5	+0.3
Financial debt (incl. IFRS 16)		1.7	3.9	-2.2
LIABILITIES		55.4	49.9	+5.5



Consolidated Cash Flow Statement

At December 31 – in €m	2025	2024	Δ
Consolidated net income	5.2	4.1	+1.1
Operating cash effect	3.0	2.7	+0.3
Cash flow from operations before net interest expense and tax	8.2	6.8	+1.4
- Tax Payments	(0.2)	(0.1)	-0.0
+ / - Change in working capital requirements from operations	(3.5)	(1.7)	-1.9
Cash-flow from operating activities (a)	4.5	5.0	-0.5
Acquisitions and scope entries	0.0	0.0	-
Net CapEx	(1.7)	(2.3)	+0.6
Cash flows from investing activities (b)	(1.7)	(2.3)	+0.6
Dividend paid	(1.7)	(1.5)	-0.2
Share buybacks	(0.1)	(0.1)	+0.1
Net borrowings	(2.0)	(2.0)	+0.1
Others	(0.2)	(0.2)	-
Cash flows from financing activities (c)	(3.9)	(3.8)	-0.1
Change in net cash (a + b + c)	(1.0)	(1.1)	+0.1
OPENING CASH	8.6	9.7	-1.1
CLOSING CASH	7.5	8.6	-1.1



2025 Key Financial Ratios

Strengthened profitability and solidity

ROCE 17,6%

Return on Capital Employed

ROE 19,2%

Return on Equity

Gearing -21%

Net financial debt to equity

Financial autonomy

49,3%

Equity as a percentage of total balance sheet

	2025	2024	Δ
ROCE (Return on Capital Employed)	17.6%	15.9%	+1.7pt
ROE (Return on Equity)	19.2%	17.5%	+1.7pt
Gearing	-21.0%	-20.0%	-1.0pt
Financial autonomy	49.3%	47.3%	+2.0pts

**A VERY ROBUST FINANCIAL STRUCTURE,
COMBINING RISING PROFITABILITY WITH ZERO DEBT**



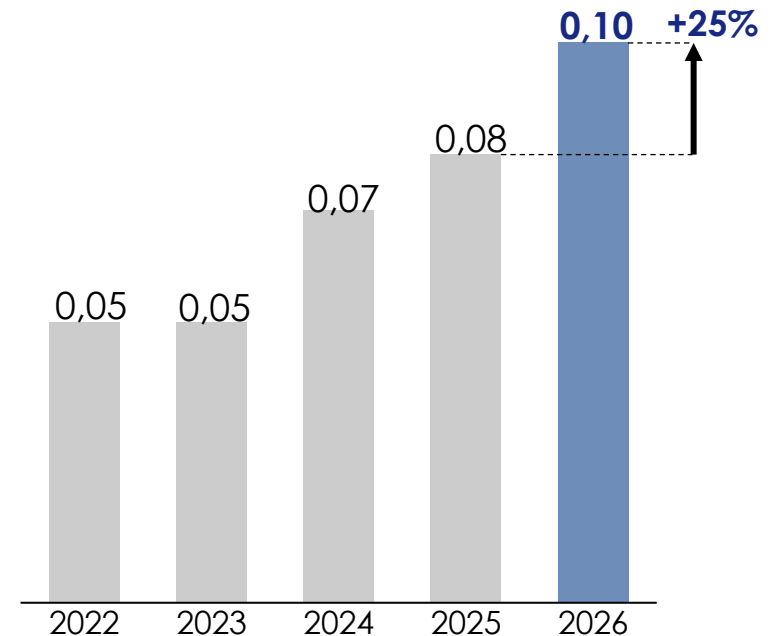
Proposed distribution to the Annual General Meeting on June 17

Distribution (per share action)	€0.10
Share price as of December 31, 2025 (per share)	€3.50
Yield	2.9%

**Cash distribution,
paid from the share premium account**

Payment date: June 24, 2026

Dividend evolution
(€ per share)

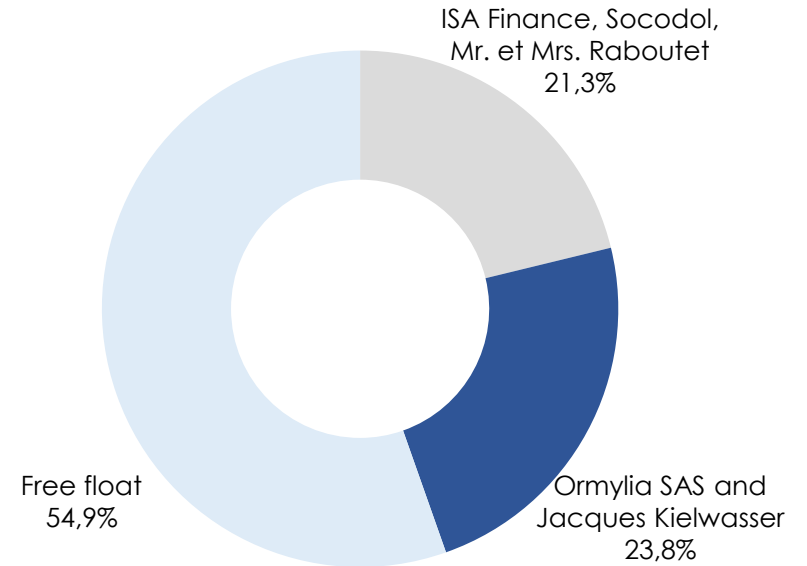


Share price performance compared to the CAC Mid & Small index



- **Market capitalization:** €117m as of April 1st, 2026
- **ISIN:** FR0000075954
- **Ticker:** ALRIB
- **Indexes** EN GROWTH ALLSHARE, EN TECH CROISSANCE
- **Bpifrance accreditation** (PEA-PME eligible)

Shareholding structure as of December 31, 2025



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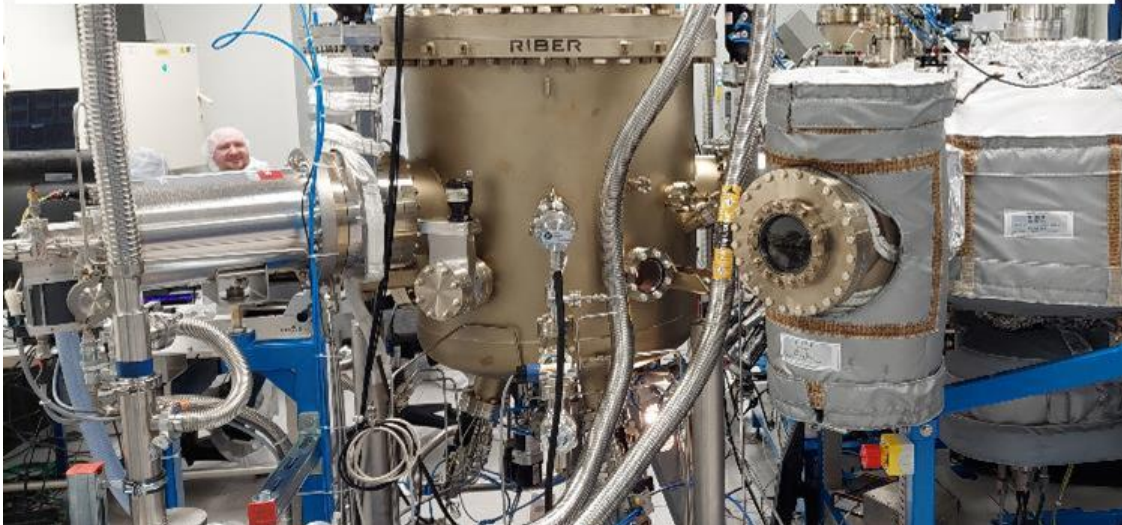


Our Development Prospects

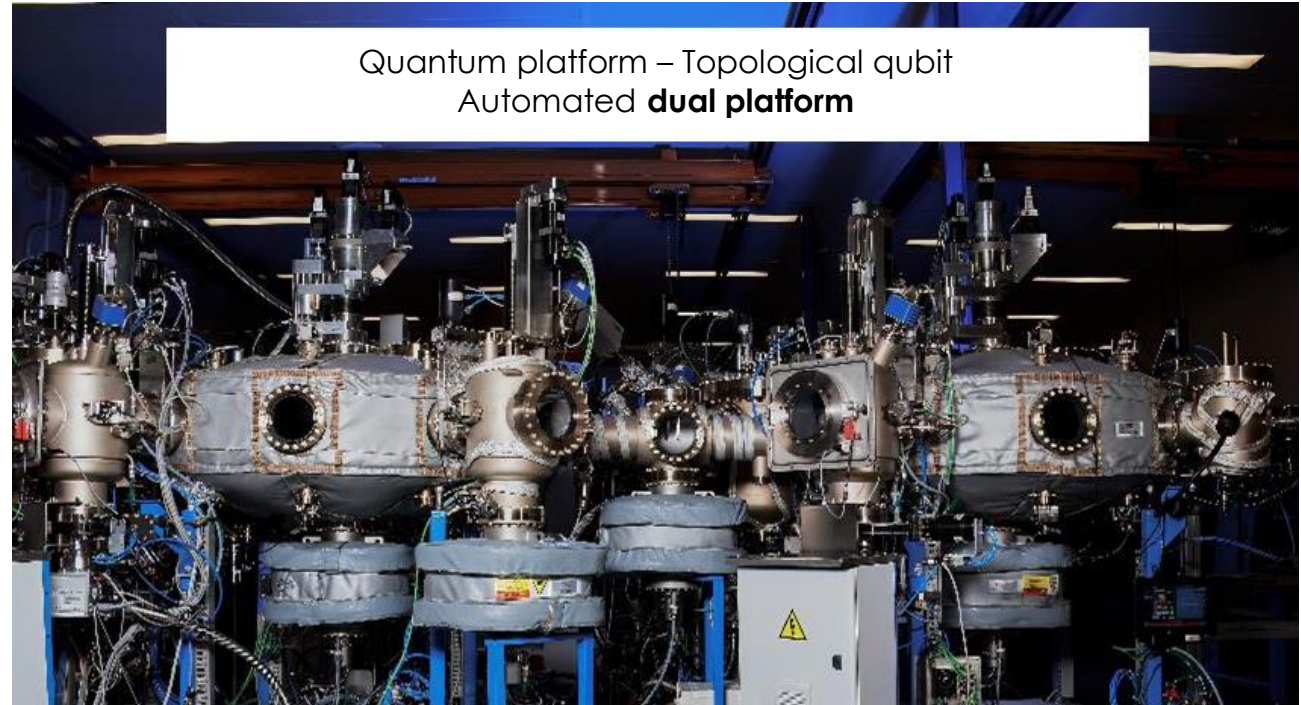
Strengthening MBE Technology

High-value hybrid platforms

Quantum platform - Topological qubit
Cold-deposition chamber at -150°C for superconducting materials
EPICENTRE project - Automated platform



Quantum platform – Topological qubit
Automated **dual platform**



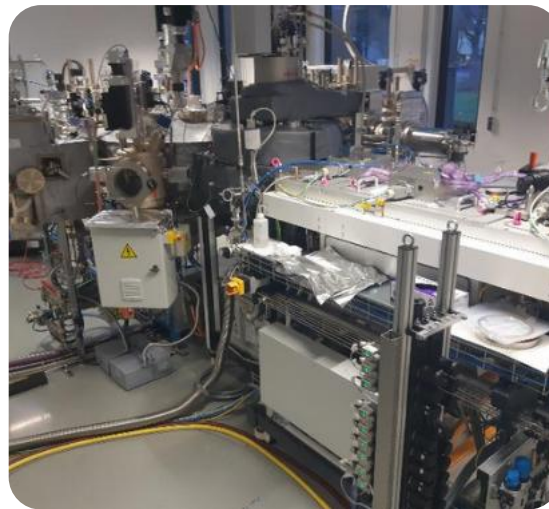
Amplifying capabilities through hybridization

Modularity



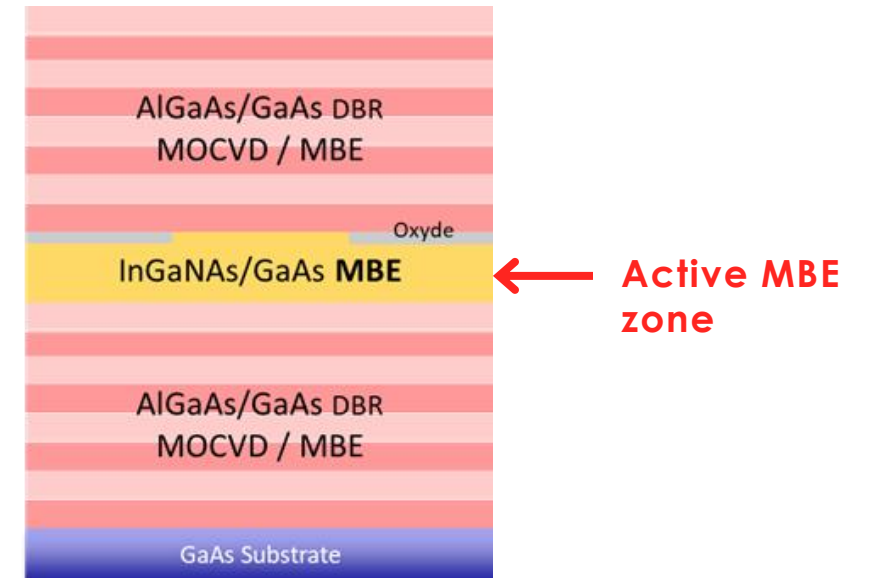
MBE + RPCVD

Flexibility

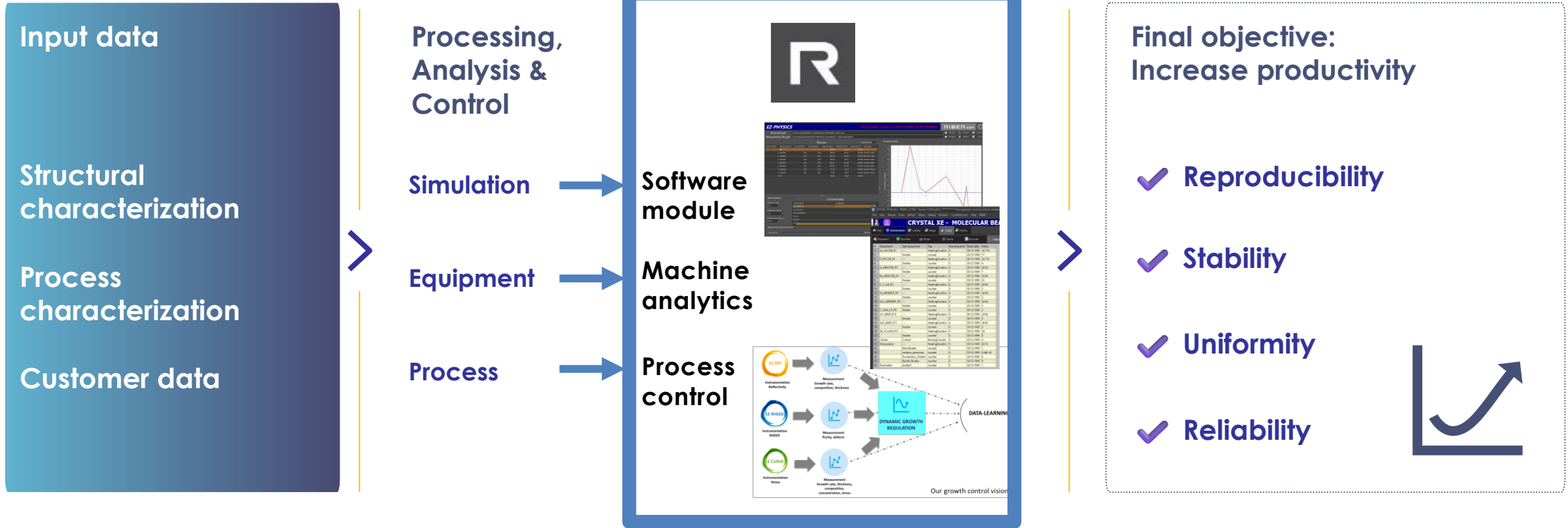


MBE + Sputtering

Versatility



Toward machine-learning-enhanced technology



RIBER



Our Development Prospects

**in silicon-based integrated
photonics**

- To address this challenge, data is transmitted in the form of a light wave.
- NVIDIA is investing \$4 billion in **photonics** for its AI data centers

source: NVIDIA – March 2026



 NVIDIA

NVIDIA and Coherent Announce Strategic Partnership to Develop Optics Technology to Scale Next-Generation Data Center Architecture

NVIDIA to Invest \$2 Billion in Coherent to Expand Supply, Deepen R&D and Advance US-Based Manufacturing

- Data rates are exploding with AI
 - Connections between servers must support speeds of: 100G => 400G => 800 G, ...
 - ... while ensuring high speed, minimal latency, low loss, and high energy efficiency.

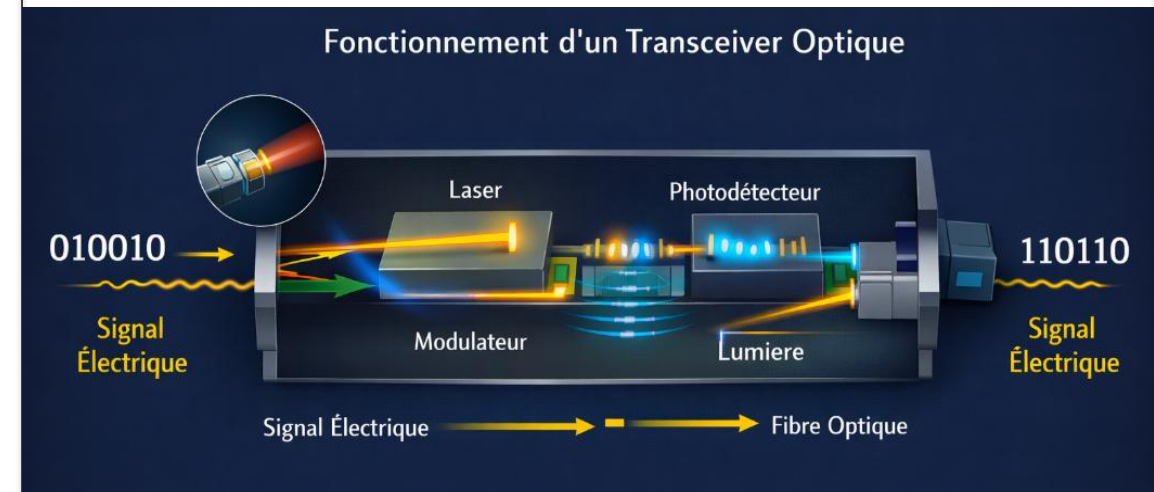
- Light now replaces copper.
 - Traditional copper interconnects can no longer keep up with this scaling.



The key role of the optical transceiver

In a data center, transceivers convert the servers' electrical data into optical signals to transport information rapidly.

- At the heart of the transceiver lies a key element: the **electro-optic modulator**



A laser remains continuously on. The electrical signal switches the light on and off, which makes it possible to encode information

- Essential compatibility with the silicon (CMOS) industry
 - The entire value chain is built on silicon: abundant, inexpensive, and available at large scale.

Comparison of Materials for Electro-Optic Modulators

Matériau	Type	Avantages	Avantages	Inconvénients	Cas d'usage
LiNbO₃ Historique / Bulk	Historique / Bulk	✓ LiNbO ₃ (Niobate de lithium)	✓ Très stable ✓ Excellente linéarité ✓ Faibles pertes	✗ Volumineux ✗ Cher ✗ Intégration difficile	Télécom longue distance, haute performance
InP III-V (composés)	InP	✓ Intègre laser + modulateur ✓ Très rapide ✓ Compact	✓ Viés rapide ✓ Compact	✗ Coût élevé ✗ Fabrication complexe	Transceivers optiques (datacenter, télécom)
GaAs / III-V	GaAs	✓ Bonnes propriétés optiques ✓ Haute vitesse	✓ Moins standard que InP	⚠ Moins standard que InP	Applications spécifiques RF / opto
Si (Photonique silicium)	Si	✓ Compatible industrie CMOS ✓ Très scalable ✓ Coût bas	✓ Effet EO faible ✓ Coût bas	✗ Effet EO faible nécessite structures complexes	Datacenters (volume, coût)
SiPh + III-V Hybride	InP	✓ Combine coût + performance ✓ laser intégré possible	✗ Complexité d'intégration	✗ Stabilité thermique limitée durée de vie	R&D, applications niche
Polymères EO		✓ Très forte efficacité EO ✓ Faible tension	✗ immature industriellement	✗ immature industriellement	Recherche avancée
BaTiO₃ Oxydes Nouvelle generation	Nouvelle generation	✓ Compact ✓ Très performant ✓ faible perte	✓ Oxipact ✓ Très performant	✗ encore coûteux	Next-gen (400G / 800G+)

Comparison of Deposition Techniques

Techniques	Crystal Quality	Advantages	Drawbacks	Maturity
MBE	★★★★★ (excellent)	- Atomic-level control - Very high quality - Clean interfaces	- Slow - Expensive	Advanced R&D
PLD (Pulsed Laser Deposition)	★★★★	- Good crystalline quality - Fast for prototyping	- Non-uniform on large surfaces - Limited scalability	R&D
CVD / MOCVD	★★★	- Industry compatible - Scalable	- Complex chemistry - Possible defects	in development
Sputtering (PVD)	★★	- Industrial - Lower cost	- Limited crystal quality - Requires annealing	Industrial (but with limited performance)

- ☐ Choosing the material is a trade-off between performance, cost, and integration
- ☐ The BTO/STO stack on silicon: a technological breakthrough for optical modulators



BTO= BaTiO₃ (Barium Titanate Oxide)
STO= SrTiO₃ (Strontium Titanate Oxide)

- The remarkable properties of BTO/STO/Si will also address the RF and quantum technology markets.

6G / 7G mobile

RF transmitter / receiver



STO on Silicon

New quantum technologies

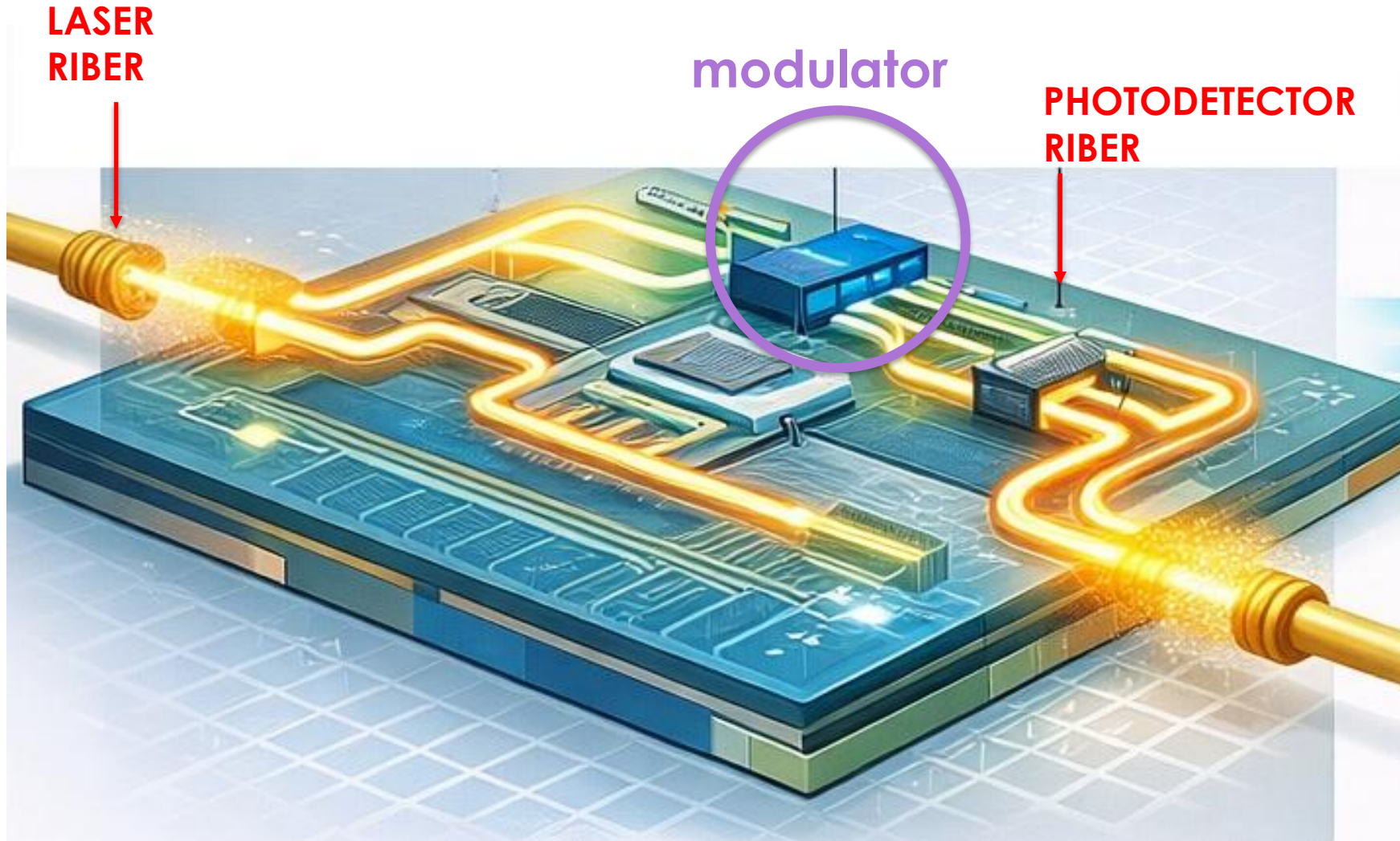
Pharmacology Finance Industrial and logistics
Chemistry Cryptography optimization

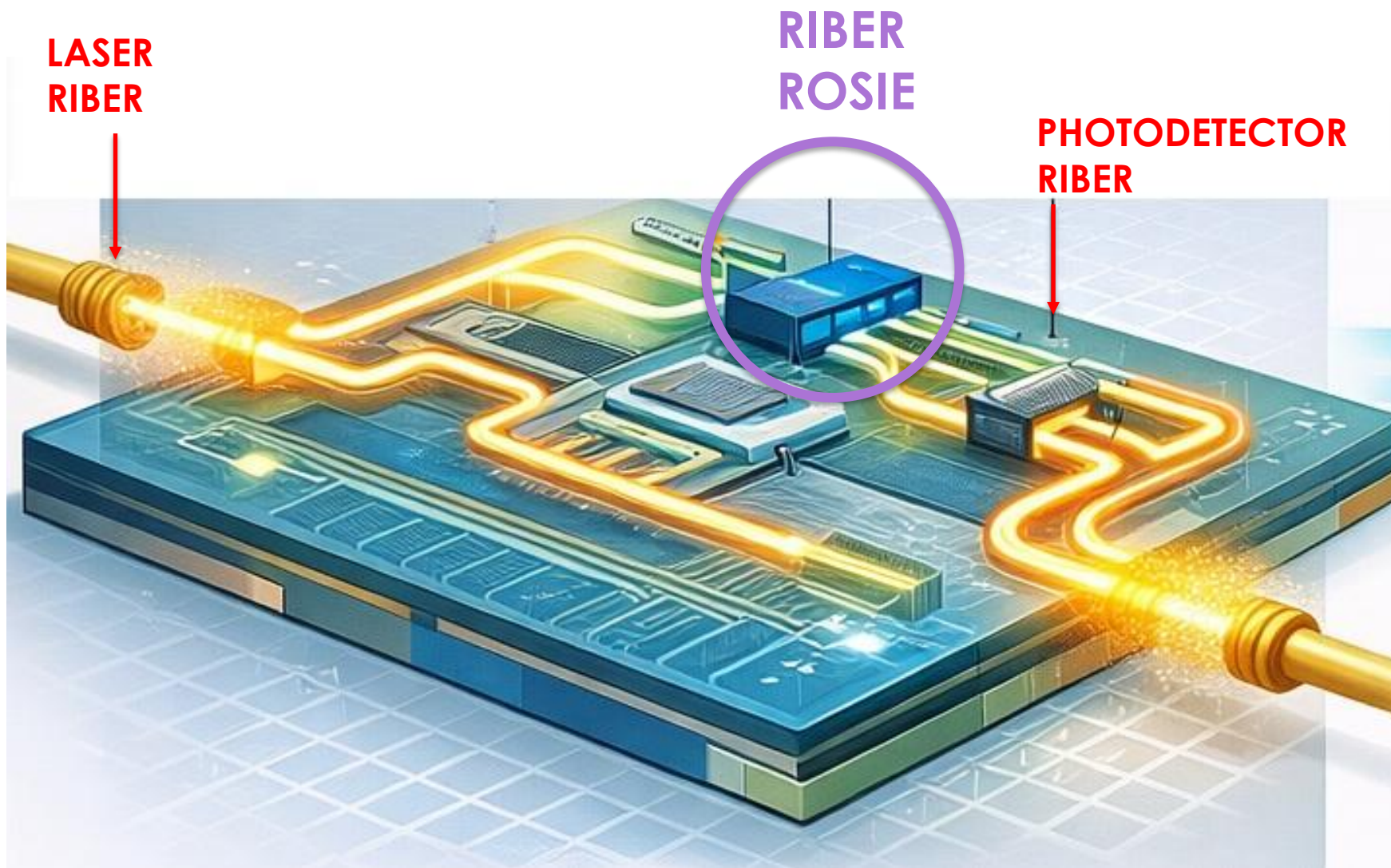


\$1-2bn in 2025
\$8-15bn in 2030
\$28-72bn in 2035

Source : McKinsey

BTO/STO on Silicon



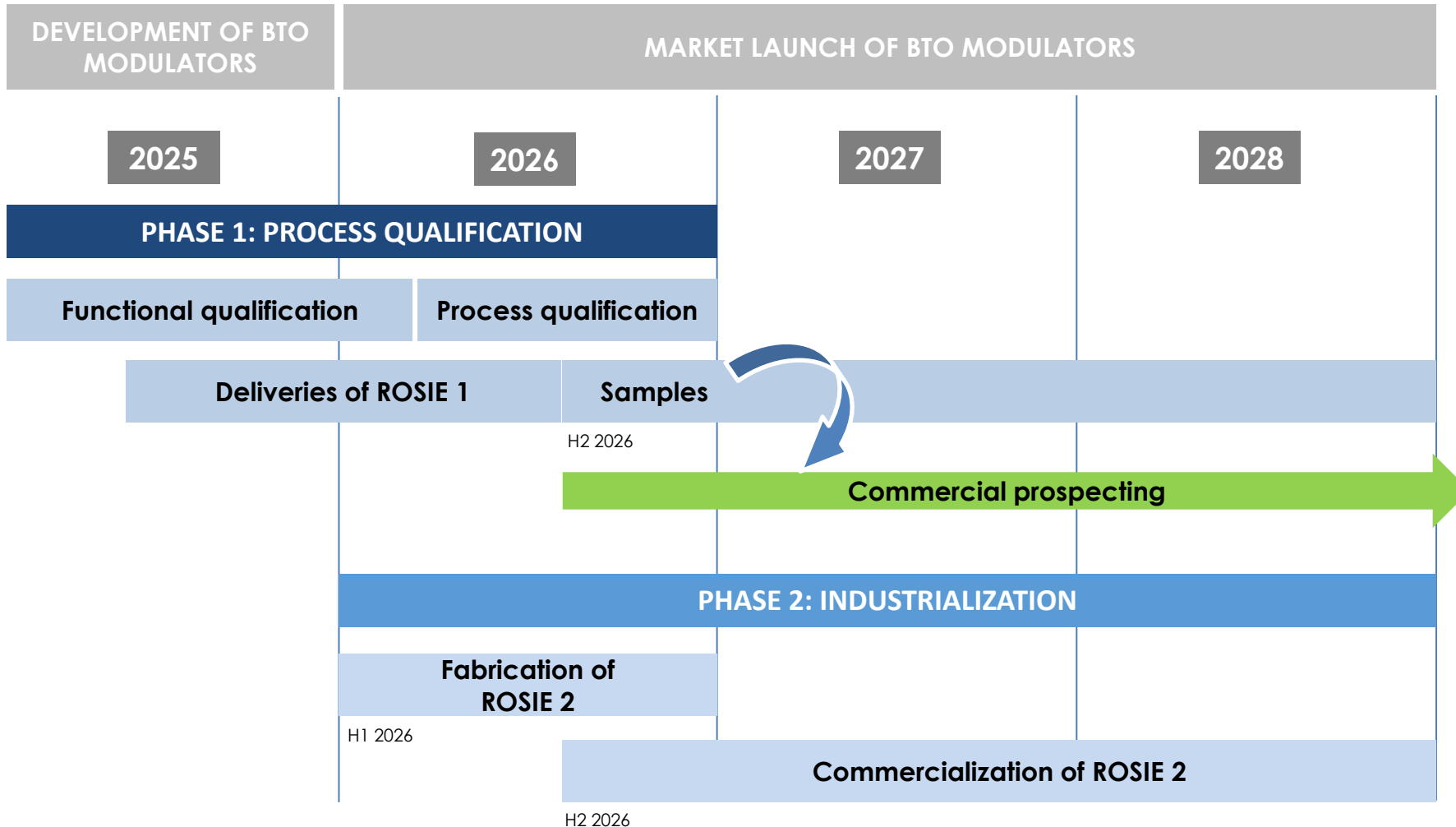


ROSIE – Riber Oxide Silicon Epitaxy

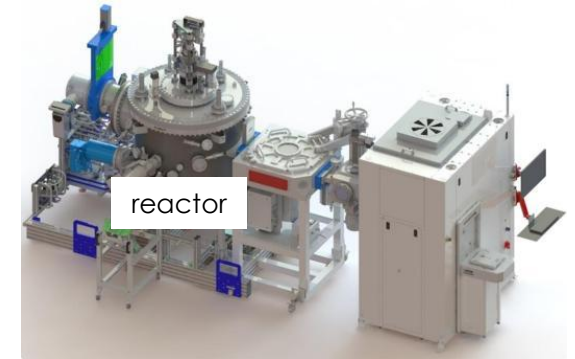
A machine compatible with the 300 mm silicon industry

A machine using a BTO/STO process to produce the next generation of electro-optic modulators.



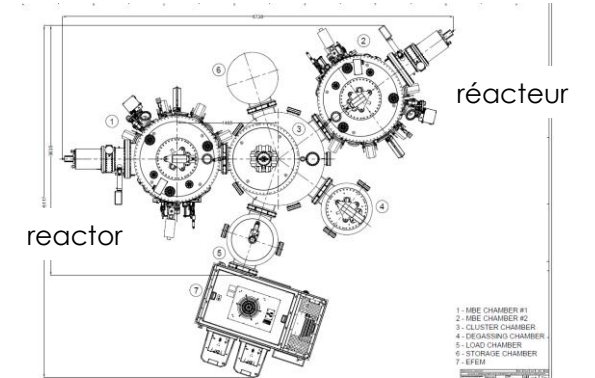


ROSIE 1



Multiply productivity

ROSIE 2

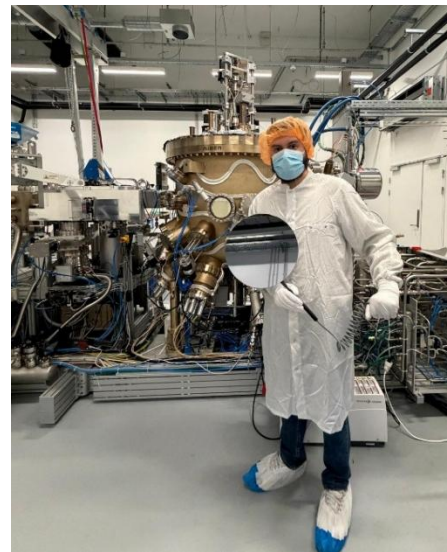


2025: POEM partnership

NQCP/NBI Denmark - EU



2025-2028



Qualification, development
of BTO processes

Quantum and Datacom/Telecom

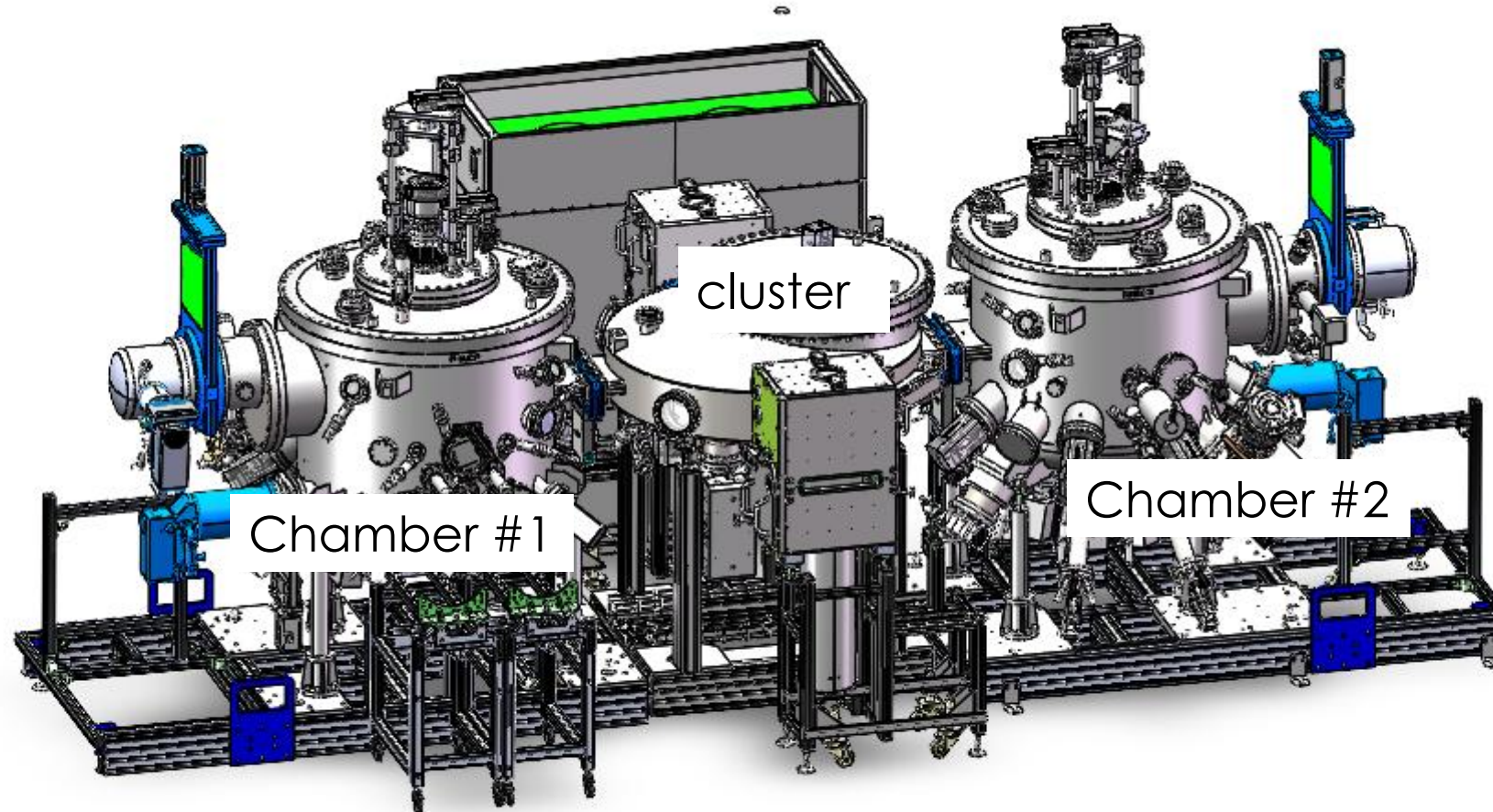
Sales / partnership / sampling / process

2026: Sale in the United States

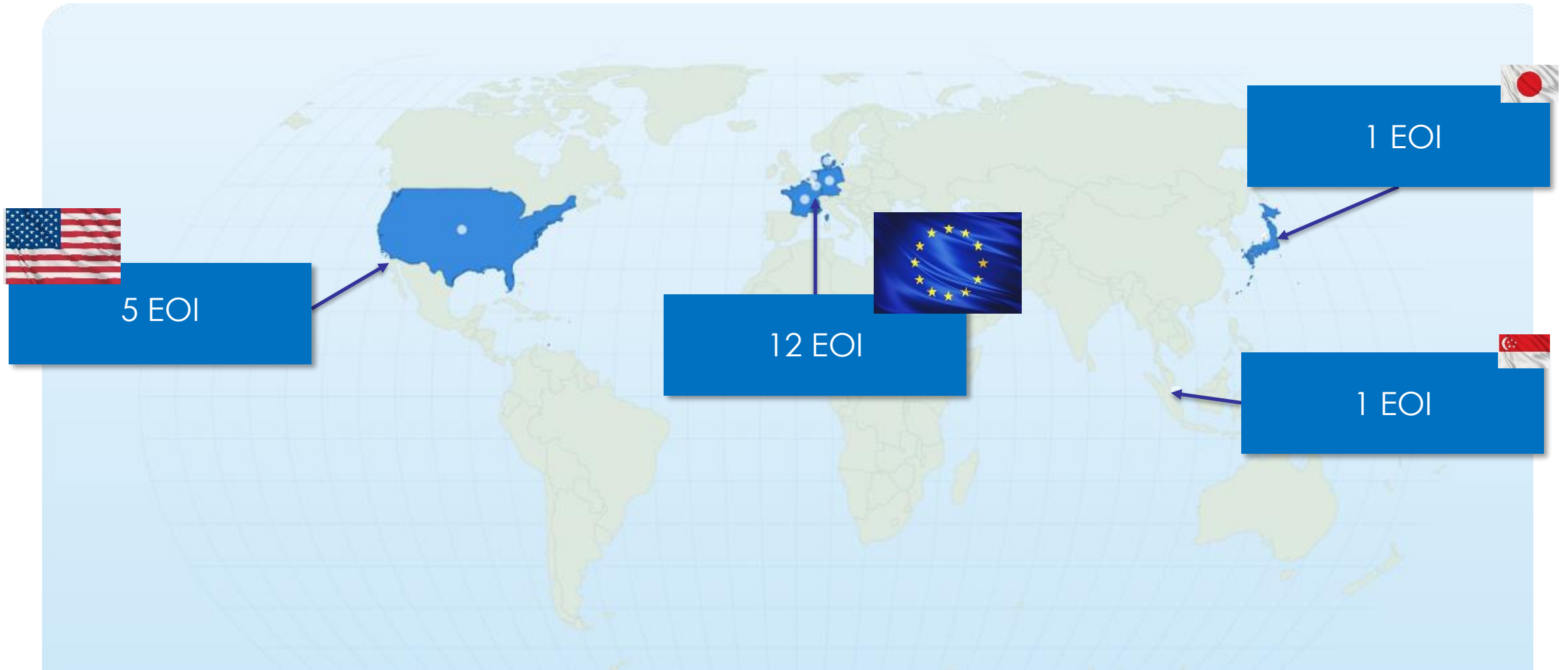


Leading player
in quantum computing
in the United States

Delivery in H1 2026



**A CLUSTER VERSION THAT INCREASES
CAPACITY, PRODUCTIVITY, AND FLEXIBILITY**

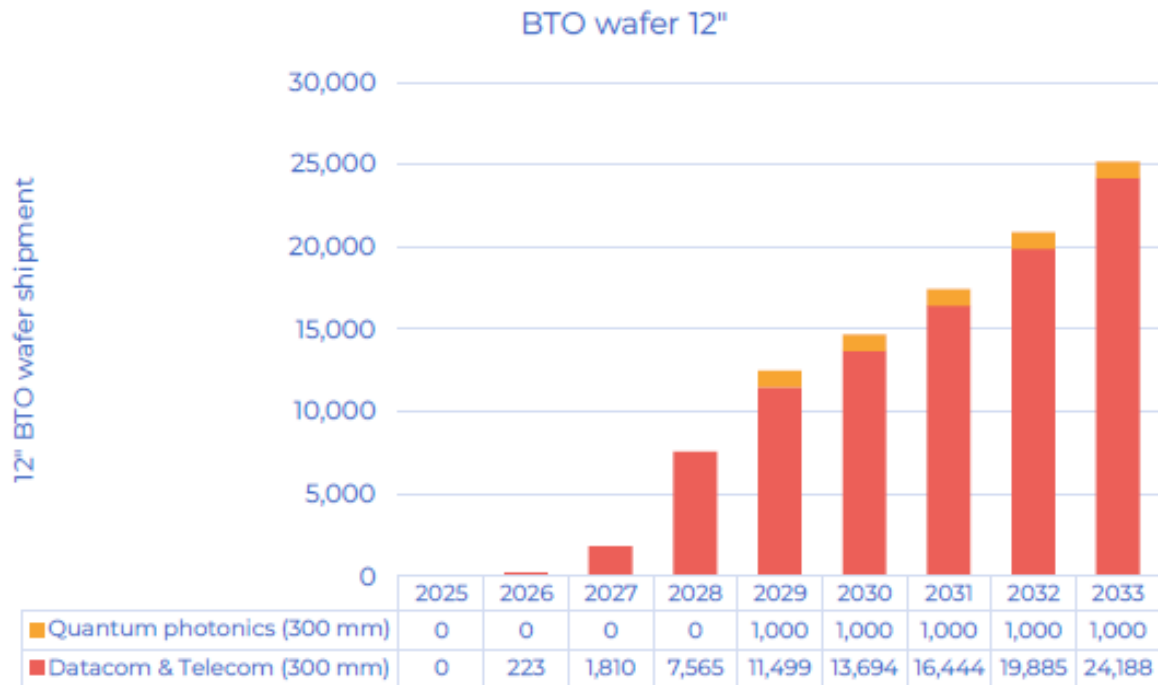


A GLOBAL INTEREST IN THE ROSIE TECHNOLOGY



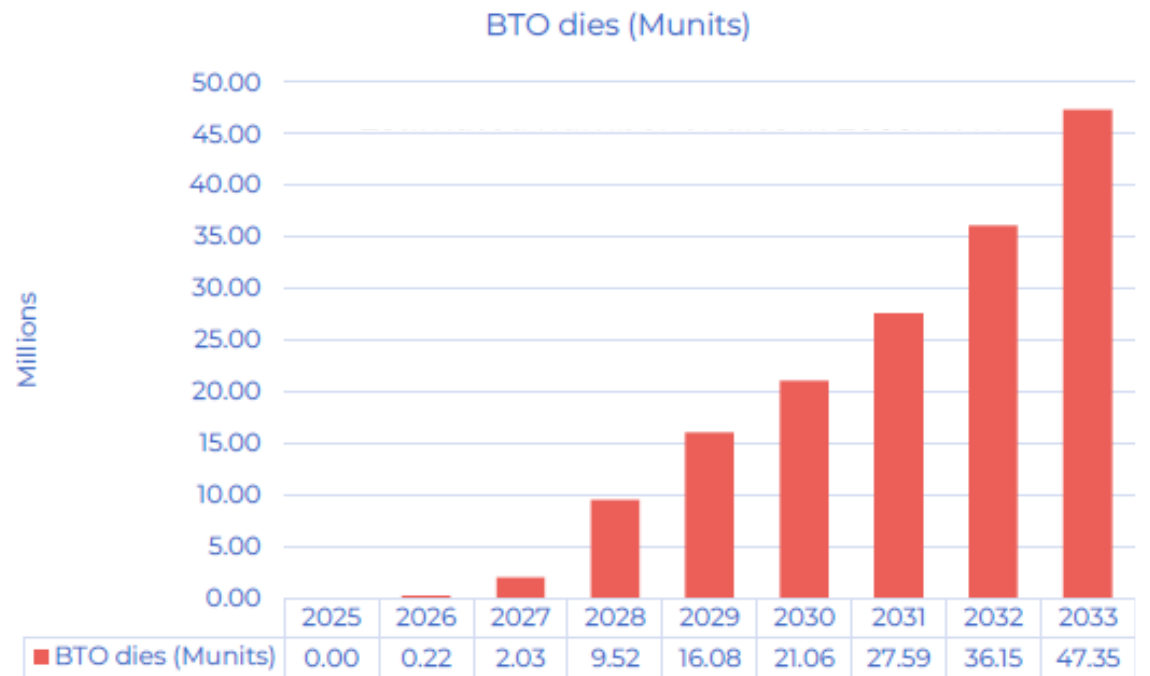
ROSIE aligned with the growth of the BTO chip market

BTO Wafers 300 mm. (in units)



Source : Yole Group 2025

BTO Chips (in millions of units)



A market opportunity with strong acceleration starting in 2027

Demand for 300 mm BTO wafers is expected to be driven by growing needs in datacom and telecom.

This dynamic supports the industrialization strategy of the ROSIE process.



From ROSIE to a 300 mm range

RIBER 300

Silicon Fab compatible



**DATAKOM
TELECOM
Q.COMPUTING
OEM**

BTO/STO

**DISPLAY
HEALTH
LED UV,
μLED**

GaInNAs/GaN

**TELECOM
Transistor RF**

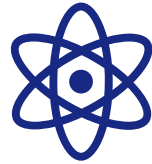
AlN/GaN

**DATAKOM
TELECOM
Laser PIC**

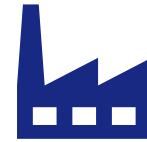
III-V



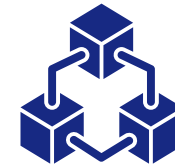
A significant improvement in our profitability



A market accelerated by AI, data infrastructures, and photonics



The first commercial validations of ROSIE and a clear trajectory toward industrialization



A differentiating technology at the heart of next-generation architectures

Objective:
turn this momentum into sustainable growth

RIBER

**a strategic player
in tomorrow's semiconductors**

Context

What is MBE (Molecular Beam Epitaxy)?

Power, richness, and performance of MBE technology

MBE is characterized by an ultra-clean environment made possible through the mastery of ultra-high vacuum. This enables atomically controlled deposition (3 Angstroms) to create nanostructures with perfect interface control.

How a nanostructure is formed:

- 1, On a heated substrate
- 2, Ultra-pure solid materials are placed in cells oriented toward the substrate. These materials are heated to high temperatures to enable their sublimation.
- 3, UHV conditions, combined with the equipment's geometry, send the atoms directly toward the surface of the substrate. The atoms then "stick" to the surface and form an atomic "layer."
- 4, Any atom that does not reach the substrate surface is trapped on a cold surface surrounding the equipment to avoid contaminating the next layer.
- 5, The stacking sequence of layers and the materials used make it possible to create nanostructures emitting light ("photonic") or electrons (electronic).

